

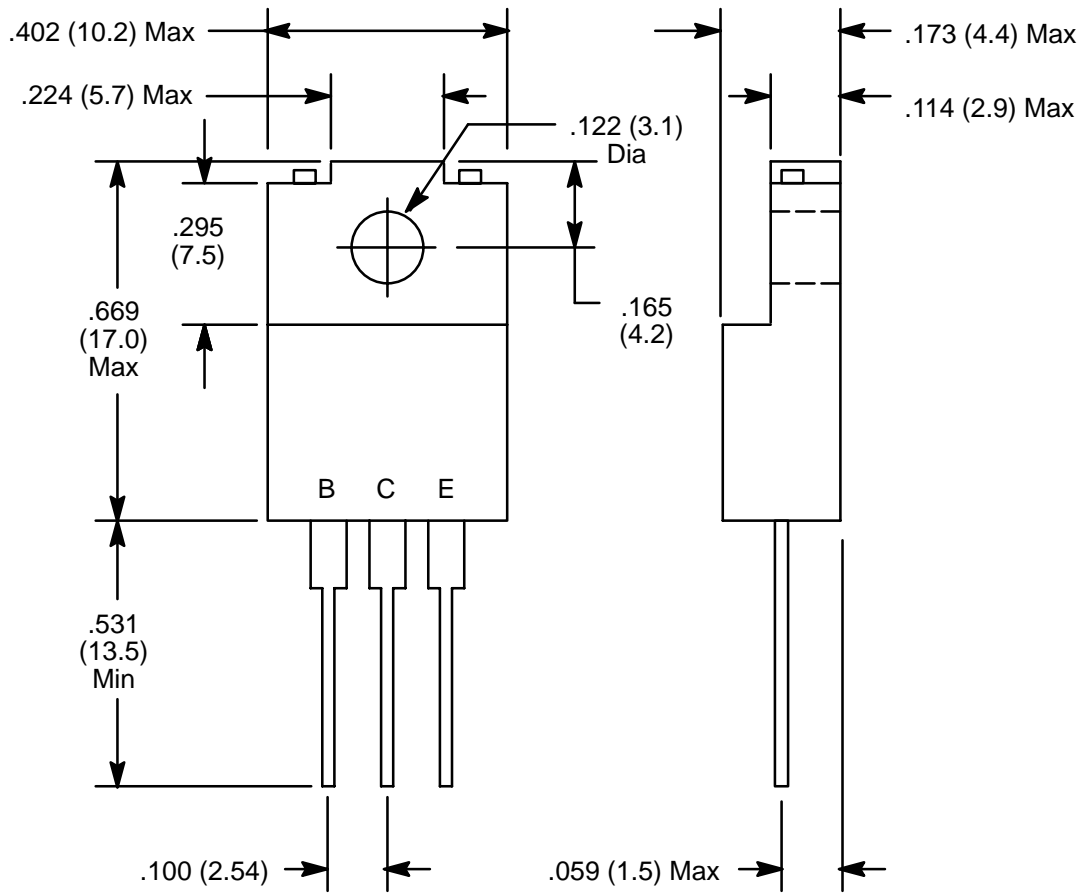
## NTE2576 (NPN) & NTE2577 (PNP) Silicon Complementary Transistors Audio Output Driver

**Absolute Maximum Ratings:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Collector–Base Voltage, $V_{CB0}$ .....	180V
Collector–Emitter Voltage, $V_{CEO}$ .....	180V
Emitter–Base Voltage, $V_{EBO}$ .....	6V
Collector Current, $I_C$ .....	2A
Base Current, $I_B$ .....	1A
Power Dissipation ( $T_C = +25^\circ\text{C}$ ), $P_C$ .....	20W
Operating Junction Temperature, $T_J$ .....	+150°C
Storage Temperature Range, $T_{stg}$ .....	–55° to +150°C

**Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 180\text{V}$	–	–	10	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 6\text{V}$	–	–	10	$\mu\text{A}$
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}$	180	–	–	V
DC Current Gain	$h_{FE}$	$V_{CE} = 10\text{V}, I_C = 700\text{mA}$	60	–	240	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 700\text{mA}, I_B = 70\text{mA}$	–	–	1.0	V
Transition Frequency	$f_T$	$V_{CE} = 12\text{V}, I_E = 700\text{mA}$	–	60	–	MHz
Output Capacitance	$C_{ob}$	$V_{CB} = 10\text{V}, f = 1\text{MHz}$	–	30	–	pF



**NOTE:** Tab is isolated